Lonten N-channel 40V, 12A, 12mΩ Power MOSFET

Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and with stand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

Features

- 40V,12A,$R_{DS(ON).max}$=12mΩ@V_{GS}=10V
- Improved dv/dt capability
- Fast switching
- Green device available

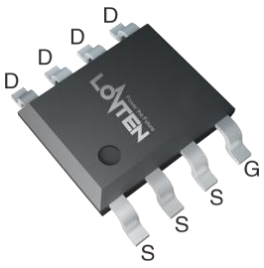
Applications

- Motor Drives
- UPS
- DC-DC Converter

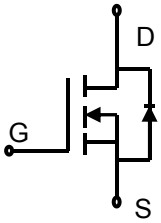
Product Summary

V_{DSS}	40V
$R_{DS(on).max}$@ V_{GS}=10V	12mΩ
I_D	12A

Pin Configuration



SOP-8



N-Channel MOSFET

Absolute Maximum Ratings

T_A= 25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	40	V
Continuous drain current (T_A =25°C)	I_D	12	A
Continuous drain current (T_A = 100°C)		7.6	A
Pulsed drain current[1)]	I_{DM}	48	A
Gate-Source voltage	V_{GSS}	±20	V
Power Dissipation (T_A =25°C)	P_D	2.1	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	59.5	°C/W

Package Marking and Ordering Information

Device	Device Package	Marking
LNL04R120	SOP-8	LNL04R120

Electrical Characteristics

T_J = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0 V, I_D=250uA	40	---	---	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.0	---	2.0	V
Drain-source leakage current	I_{DSS}	V_{DS}=40 V, V_{GS}=0 V, T_J = 25°C	---	---	1	μA
		V_{DS}=32 V, V_{GS}=0 V, T_J = 125°C	---	---	10	μA
Gate leakage current, Forward	I_{GSSF}	V_{GS}=20 V, V_{DS}=0 V	---	---	100	nA
Gate leakage current, Reverse	I_{GSSR}	V_{GS}=-20 V, V_{DS}=0 V	---	---	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=12 A	---	9.2	12	mΩ
		V_{GS}=4.5 V, I_D=8 A	---	11.8	16	mΩ
Forward transconductance	g_{fs}	V_{DS} =5 V , I_D=20A	---	35	---	S
Dynamic characteristics						
Input capacitance	C_{iss}	V_{DS} = 20 V, V_{GS} = 0 V, F = 1MHz	---	1370	---	pF
Output capacitance	C_{oss}		---	158	---	
Reverse transfer capacitance	C_{rss}		---	125	---	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 20V,V_{GS}=10V, I_D =12 A	---	14.5	---	ns
Rise time	t_r		---	19.2	---	
Turn-off delay time	$t_{d(off)}$		---	61	---	
Fall time	t_f		---	27	---	
Gate resistance	R_g	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	3.5	---	Ω
Gate charge characteristics						
Gate to source charge	Q_{gs}	V_{DS}=20V, I_D=12A, V_{GS}= 10V	---	7.1	---	nC
Gate to drain charge	Q_{gd}		---	2.9	---	
Gate charge total	Q_g		---	27.5	---	
Drain-Source diode characteristics and Maximum Ratings						
Continuous Source Current	I_S		---	---	12	A
Pulsed Source Current[3)]	I_{SM}		---	---	48	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=10A, T_J=25℃	---	---	1.2	V
Reverse Recovery Time	t_{rr}	I_S=12A,di/dt=100A/us, T_J=25℃	---	21	---	ns
Reverse Recovery Charge	Q_{rr}		---	7.8	---	nC

Notes:

1: Repetitive Rating: Pulse width limited by maximum junction temperature.

2: Pulse Test：Pulse Width ≤300μs, Duty Cycle≤2%.

Electrical Characteristics Diagrams

Figure 1. Typ. Output Characteristics

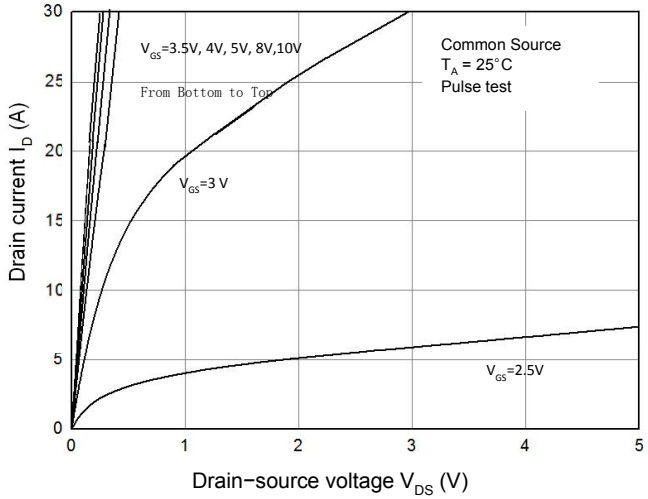


Figure 2. Transfer Characteristics

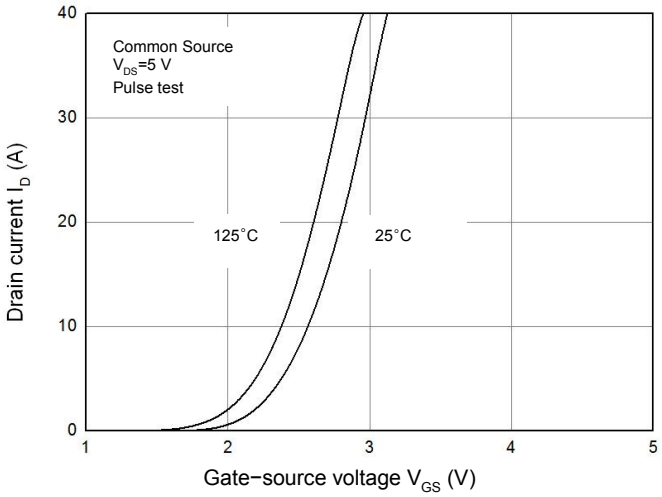


Figure 3. Capacitance Characteristics

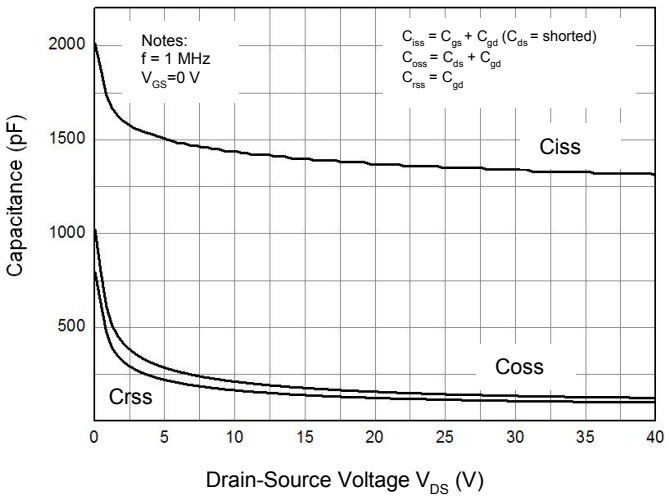


Figure 4. Gate Charge Waveform

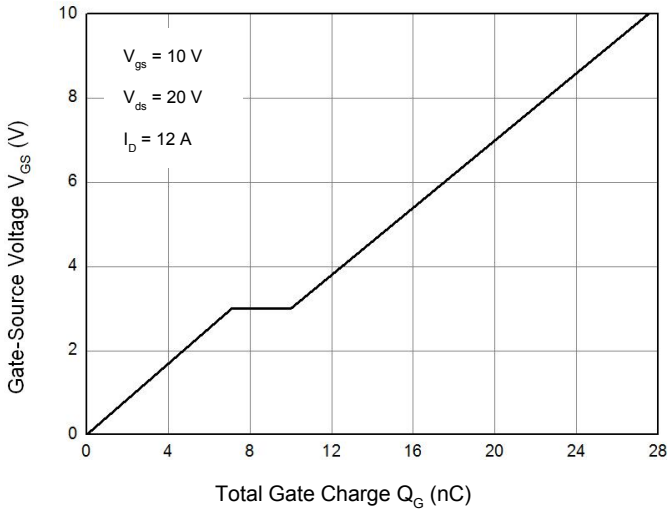


Figure 5. Body-Diode Characteristics

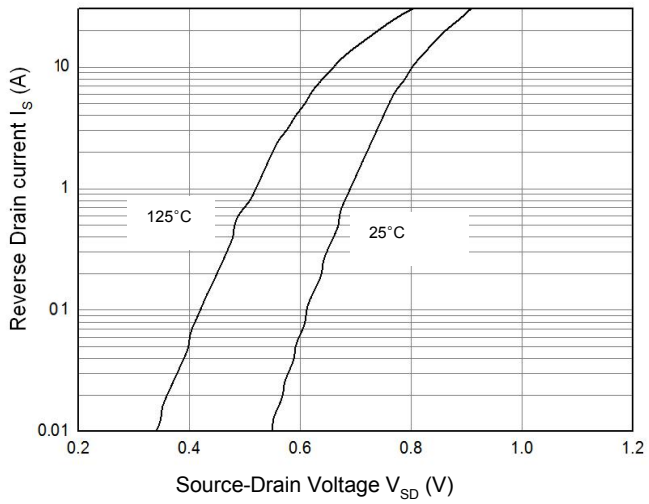


Figure 6. Rdson-Drain Current

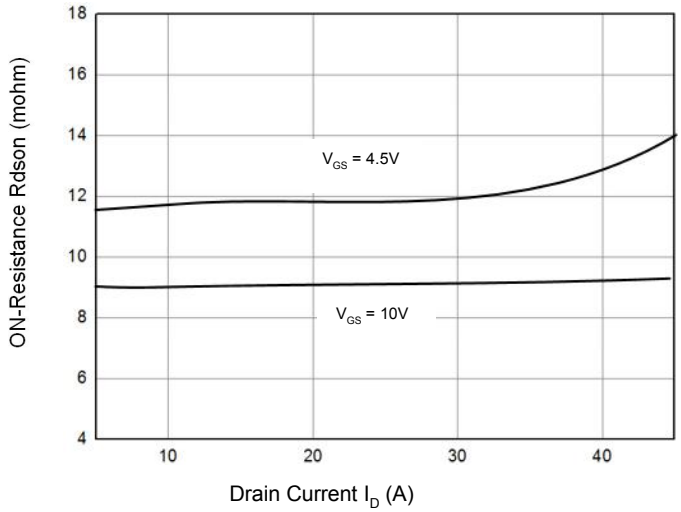


Figure 7. Rdson-Junction Temperature(℃)

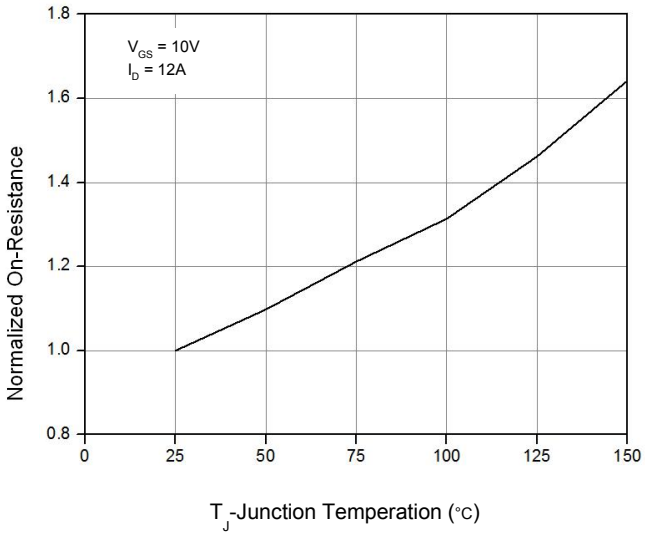


Figure 8. Maximum Safe Operating Area

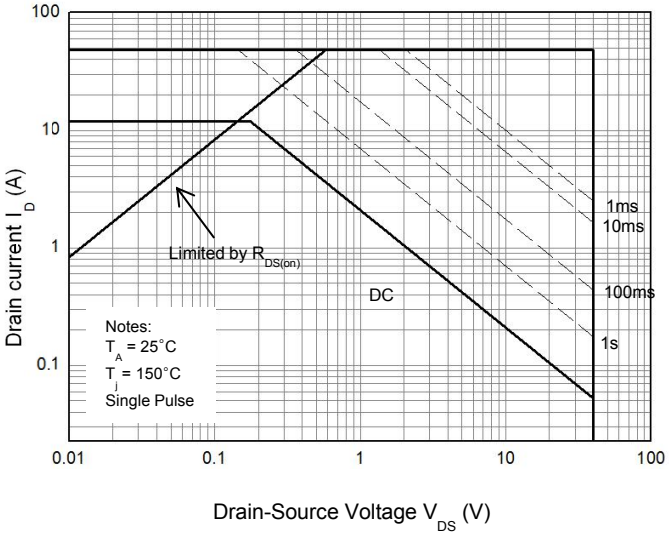
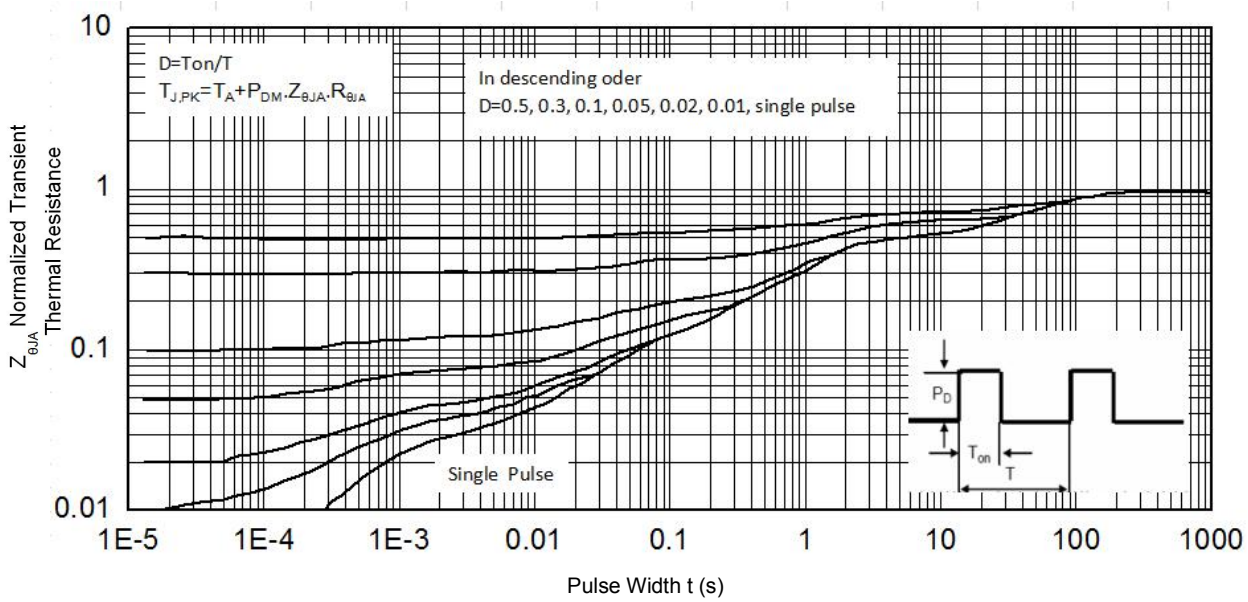


Figure 9. Normalized Maximum Transient Thermal Impedance (RthJA)



Test Circuit & Waveform

Figure 8. Gate Charge Test Circuit & Waveform

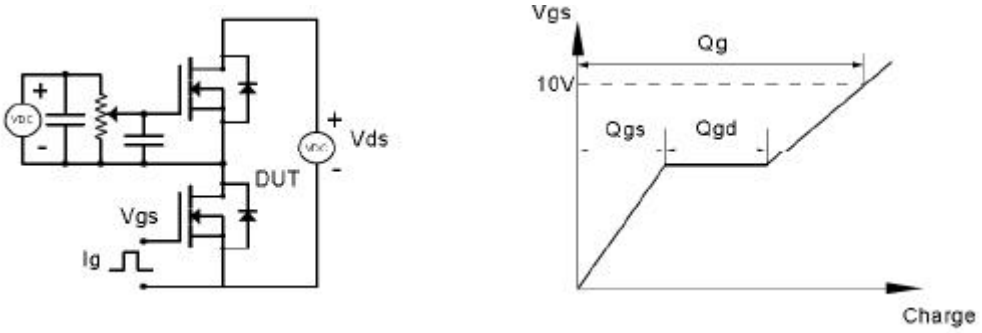


Figure 9. Resistive Switching Test Circuit & Waveforms

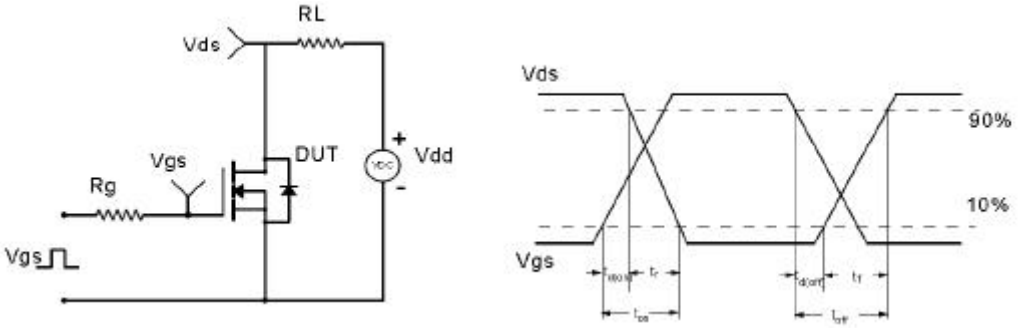


Figure 10. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

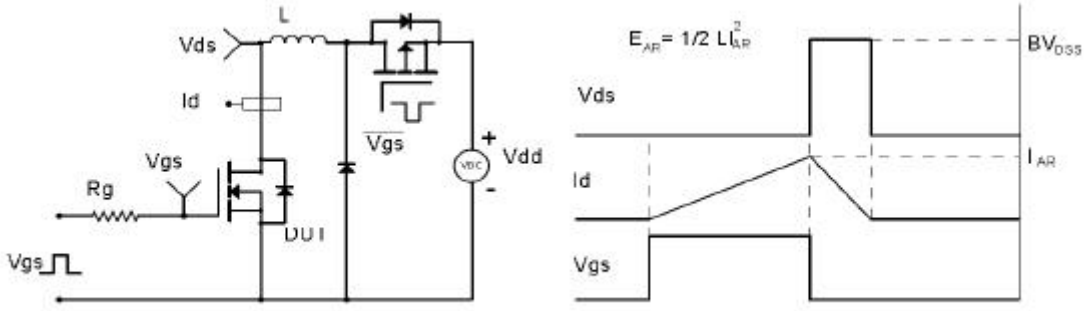
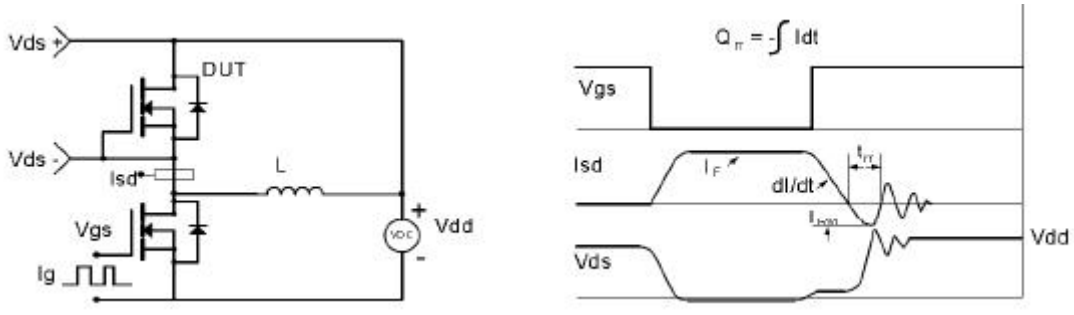
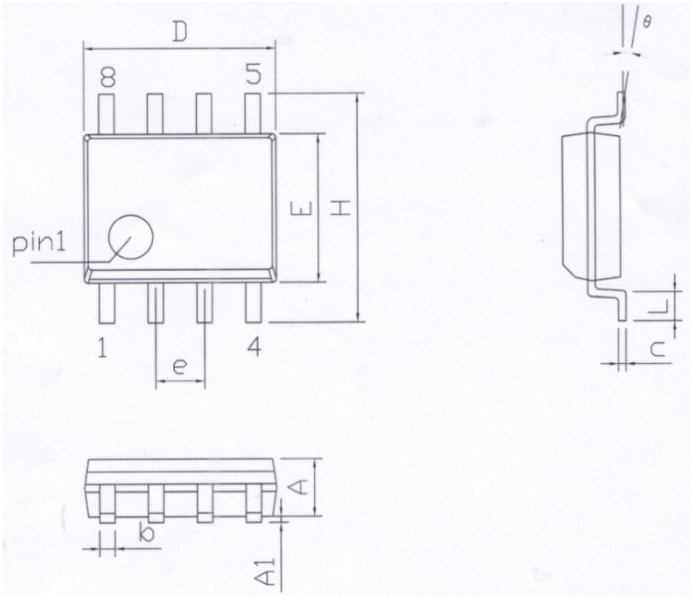


Figure 11. Diode Recovery Circuit & Waveform

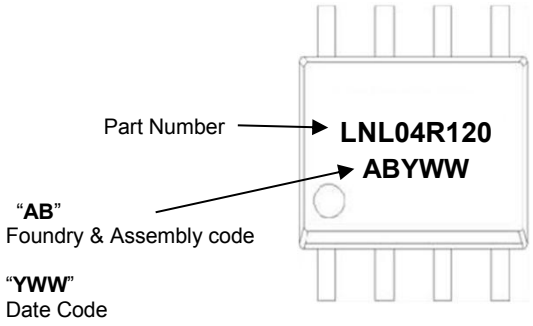


Mechanical Dimensions for SOP-8



COMMON DIMENSIONS				
SYMBOL	MILLIMETERS		INCHS	
	MIN	MAX	MIN	MAX
A	1.35	1.65	0.053	0.065
A1	0.10	0.25	0.004	0.010
b	0.35	0.50	0.014	0.020
c	0.19	0.27	0.007	0.011
D	4.80	5.10	0.189	0.201
E	3.80	4.10	0.150	0.161
e	1.22	1.32	0.048	0.052
H	5.80	6.20	0.228	0.244
L	0.60	0.90	0.024	0.035
θ	0°	8°	0°	8°

SOP-8 Part Marking Information



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